

Document Title

**128Kx8 Bit High Speed Static RAM(5V Operating), Evolutionary Pin out.
Operated at Commercial and Industrial Temperature Range.**

Revision History

<u>Rev.No.</u>	<u>History</u>	<u>Draft Data</u>	<u>Remark</u>
Rev. 0.0	Initial release with Design Target.	Feb. 1st, 1997	Design Target
Rev. 1.0	Release to Preliminary Data Sheet. 1. Replace Design Target to Preliminary.	Jun. 1st, 1997	Preliminary
Rev. 2.0	Release to Final Data Sheet. 1. Delete Preliminary. 2. Delete 17ns, L-version and Industrial Temperature Part. 3. Delete Voh1=3.95V. 4. Delete Data Retention Characteristics and Wave form. 5. Relax operating current	Feb. 6th. 1998	Final

Speed	Previous	Now
15ns	130mA	125mA
17ns	120mA	-
20ns	110mA	123mA

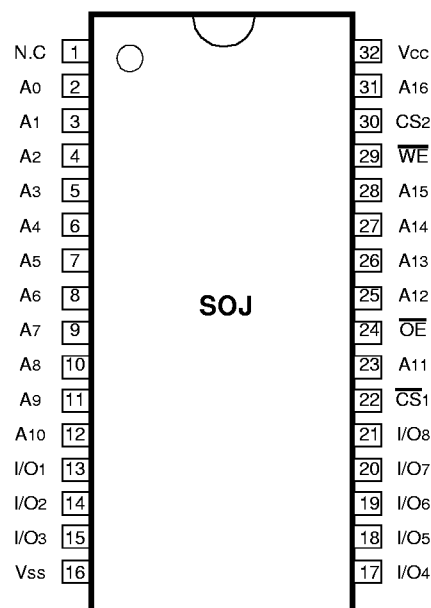
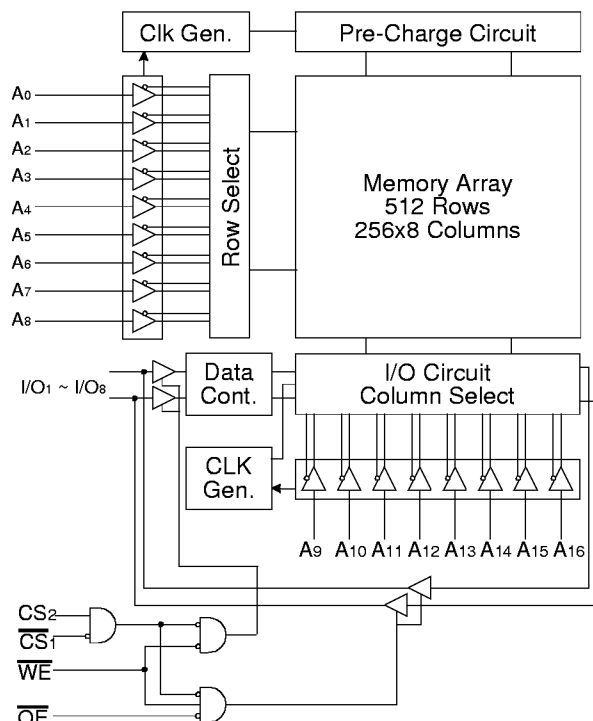
The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions on the parameters of this device. If you have any questions, please contact the SAMSUNG branch office near your office, call or contact Headquarters.

128K x 8 Bit High-Speed CMOS Static RAM
FEATURES

- Fast Access Time 15, 20ns(Max.)
- Low Power Dissipation
 - Standby (TTL) : 20mA(Max.)
 - (CMOS) : 5mA(Max.)
- Operating KM681001B - 15 : 125mA(Max.)
- KM681001B - 20 : 123mA(Max.)
- Single 5.0V±10% Power Supply
- TTL Compatible Inputs and Outputs
- Fully Static Operation
 - No Clock or Refresh required
- Three State Outputs
- Standard Pin Configuration
 - KM681001BJ : 32-SOJ-400
 - KM681001BSJ : 32-SOJ-300

GENERAL DESCRIPTION

The KM681001B is a 1,048,576-bit high-speed Static Random Access Memory organized as 131,072 words by 8 bits. The KM681001B uses 8 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. The device is fabricated using Samsung's advanced CMOS process and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications. The KM681001B is packaged in a 400/300 mil 32-pin plastic SOJ.

PIN CONFIGURATION (Top View)

FUNCTIONAL BLOCK DIAGRAM

PIN FUNCTION

Pin Name	Pin Function
A0 - A16	Address Inputs
$\overline{WE}$	Write Enable
$\overline{CS1}$, CS2	Chip Selects
$\overline{OE}$	Output Enable
I/O1 ~ I/O8	Data Inputs/Outputs
Vcc	Power(+5.0V)
Vss	Ground
N.C	No Connection

ABSOLUTE MAXIMUM RATINGS*

Parameter	Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss	V _{IN} , V _{OUT}	-0.5 to 7.0	V
Voltage on Vcc Supply Relative to Vss	V _{CC}	-0.5 to 7.0	V
Power Dissipation	P _D	1.0	W
Storage Temperature	T _{STG}	-65 to 150	°C
Operating Temperature	T _A	0 to 70	°C

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS(T_A=0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
Ground	V _{SS}	0	0	0	V
Input High Voltage	V _{IH}	2.2	-	V _{CC} +0.5**	V
Input Low Voltage	V _{IL}	-0.5*	-	0.8	V

NOTE: * V_{IL}(Min) = -2.0V a.c(Pulse Width≤10ns) for I_S≤20mA

** V_{IH}(Max) = V_{CC} + 2.0V a.c (Pulse Width≤10ns) for I_S≤20mA

DC AND OPERATING CHARACTERISTICS(T_A=0 to 70°C, V_{CC}=5.0V±10%, unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Max	Unit
Input Leakage Current	I _{LI}	V _{IN} = V _{SS} to V _{CC}		-2	2	μA
Output Leakage Current	I _{LO}	$\overline{CS}_1=V_{IH}$ or CS ₂ =V _{IL} or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{OUT} = V _{SS} to V _{CC}		-2	2	μA
Operating Current	I _{CC}	Min. Cycle, 100% Duty $\overline{CS}_1=V_{IL}$, CS ₂ =V _{IH} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	15ns	-	125	mA
			20ns	-	123	
Standby Current	I _{SB}	Min. Cycle, $\overline{CS}_1=V_{IH}$ or CS ₂ =V _{IL}		-	20	mA
	I _{SB1}	f=0MHz, $\overline{CS}_1 \geq V_{CC}-0.2V$ or CS ₂ ≤0.2V, V _{IN} ≥V _{CC} -0.2V or V _{IN} ≤0.2V		-	5	
Output Low Voltage Level	V _{OL}	I _{OL} =8mA		-	0.4	V
Output High Voltage Level	V _{OH}	I _{OH} =-4mA		2.4	-	V

CAPACITANCE*(T_A=25°C, f=1.0MHz)

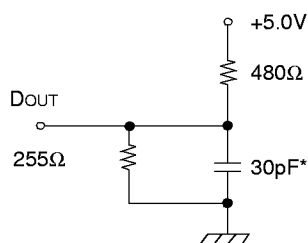
Item	Symbol	Test Conditions	MIN	Max	Unit
Input/Output Capacitance	C _{I/O}	V _{I/O} =0V	-	8	pF
Input Capacitance	C _{IN}	V _{IN} =0V	-	6	pF

* NOTE : Capacitance is sampled and not 100% tested.

AC CHARACTERISTICS($T_A=0$ to 70°C , $V_{CC}=5.0\text{V}\pm 10\%$, unless otherwise noted.)**TEST CONDITIONS**

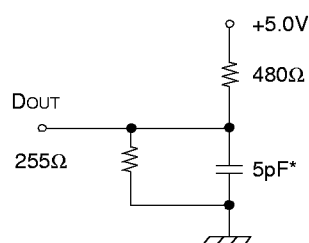
Parameter	Value
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3ns
Input and Output timing Reference Levels	1.5V
Output Loads	See below

Output Loads(A)



Output Loads(B)

for tHZ, tLZ, tWHZ, tOW, tOLZ & tOHZ



* Including Scope and Jig Capacitance

READ CYCLE

Parameter	Symbol	KM681001B-15		KM681001B-20		Unit
		Min	Max	Min	Max	
Read Cycle Time	t _{RC}	15	-	20	-	ns
Address Access Time	t _{AA}	-	15	-	20	ns
Chip Select to Output	t _{CO} *	-	15	-	20	ns
Output Enable to Valid Output	t _{OE}	-	8	-	10	ns
Chip Enable to Low-Z Output	t _{LZ} *	3	-	3	-	ns
Output Enable to Low-Z Output	t _{OLZ}	0	-	0	-	ns
Chip Disable to High-Z Output	t _{HZ} *	0	6	0	8	ns
Output Disable to High-Z Output	t _{OHZ}	0	6	0	8	ns
Output Hold from Address Change	t _{OH}	3	-	3	-	ns
Chip Selection to Power Up Time	t _{PU}	0	-	0	-	ns
Chip Selection to Power Down Time	t _{PD}	-	15	-	20	ns

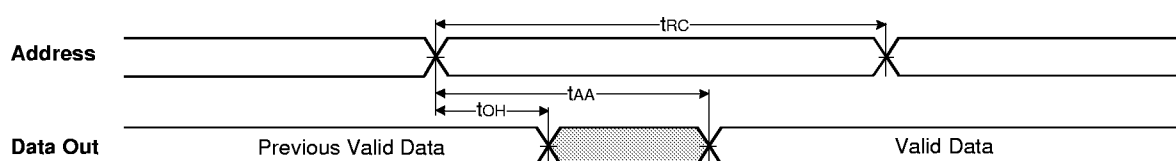
NOTE : t_{CO}=t_{CO1}, t_{CO2} / t_{LZ}=t_{LZ1}, t_{LZ2} / t_{HZ}=t_{HZ1}, t_{HZ2}

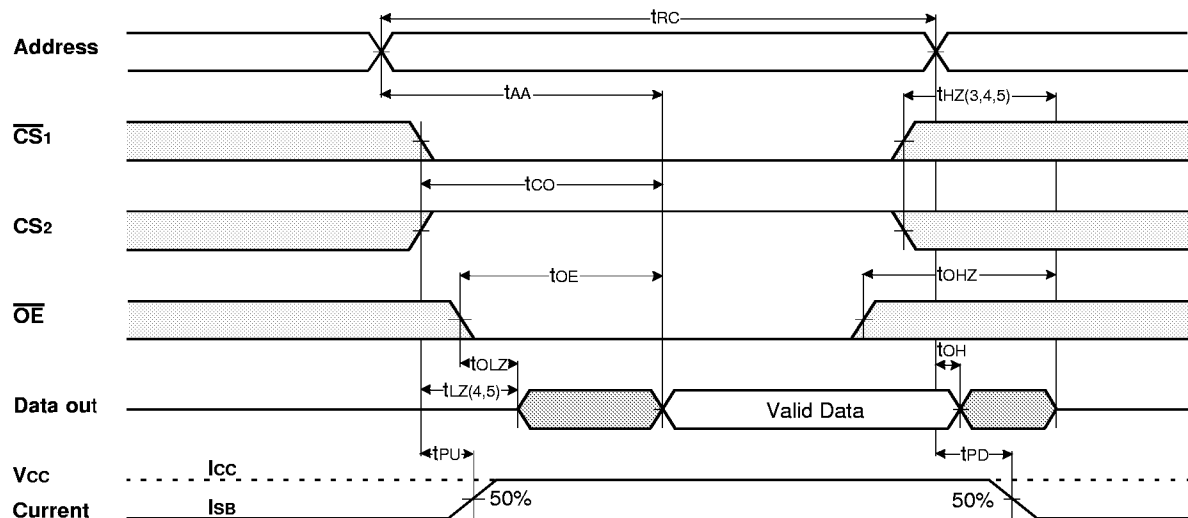
WRITE CYCLE

Parameter	Symbol	KM681001B-15		KM681001B-20		Unit
		Min	Max	Min	Max	
Write Cycle Time	t _{WC}	15	-	20	-	ns
Chip Select to End of Write	t _{CW}	10	-	12	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	ns
Address Valid to End of Write	t _{AW}	10	-	12	-	ns
Write Pulse Width($\overline{OE}$ High)	t _{WP}	10	-	12	-	ns
Write Pulse Width($\overline{OE}$ Low)	t _{WP1}	15	-	20	-	ns
Write Recovery Time	t _{WR} *	0	-	0	-	ns
Write to Output High-Z	t _{WHZ}	0	8	0	10	ns
Data to Write Time Overlap	t _{DW}	7	-	9	-	ns
Data Hold from Write Time	t _{DH}	0	-	0	-	ns
End Write to Output Low-Z	t _{OW}	3	-	3	-	ns

NOTE : t_{WR} = t_{WR1}, t_{WR2}

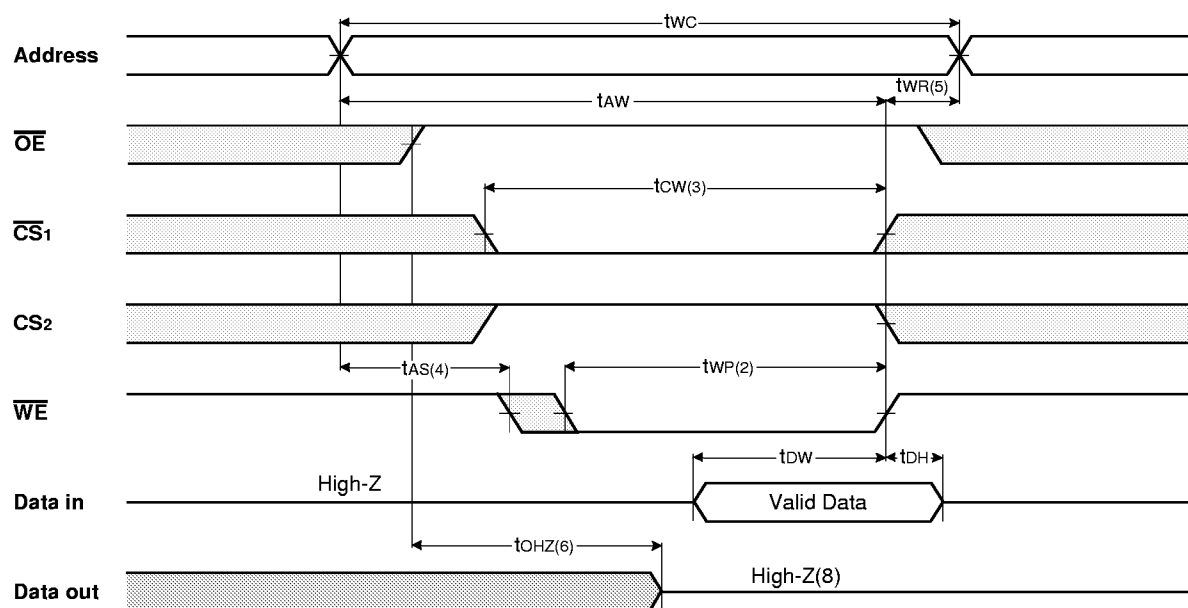
TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS}_1 = \overline{OE} = V_{IL}$, $CS_2 = \overline{WE} = V_{IH}$)

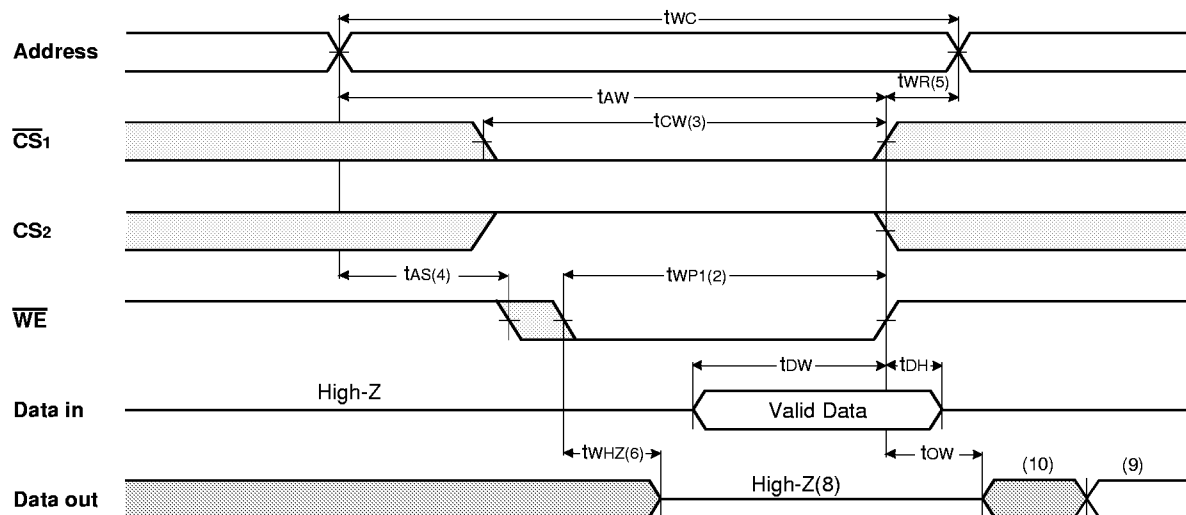
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)

NOTES(READ CYCLE)

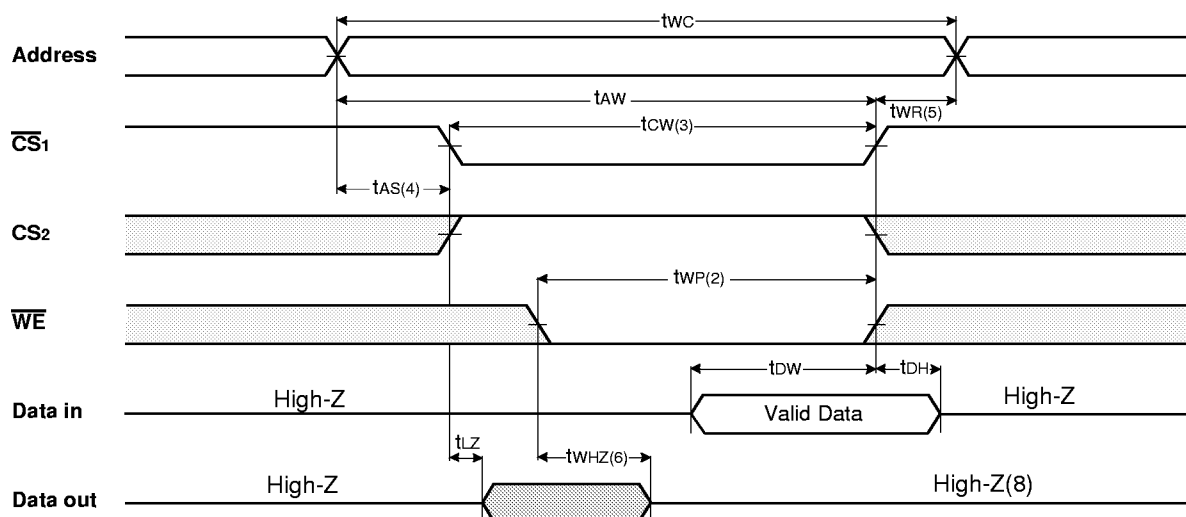
1. $\overline{WE}$ is high for read cycle.
2. All read cycle timing is referenced from the last valid address to the first transition address.
3. t_{HZ} and t_{OH} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device.
5. Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with $\overline{CS1}=V_{IL}$ and $CS2=V_{IH}$.
7. Address valid prior to coincident with $\overline{CS1}$ transition low and $CS2$ transition high.
8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.

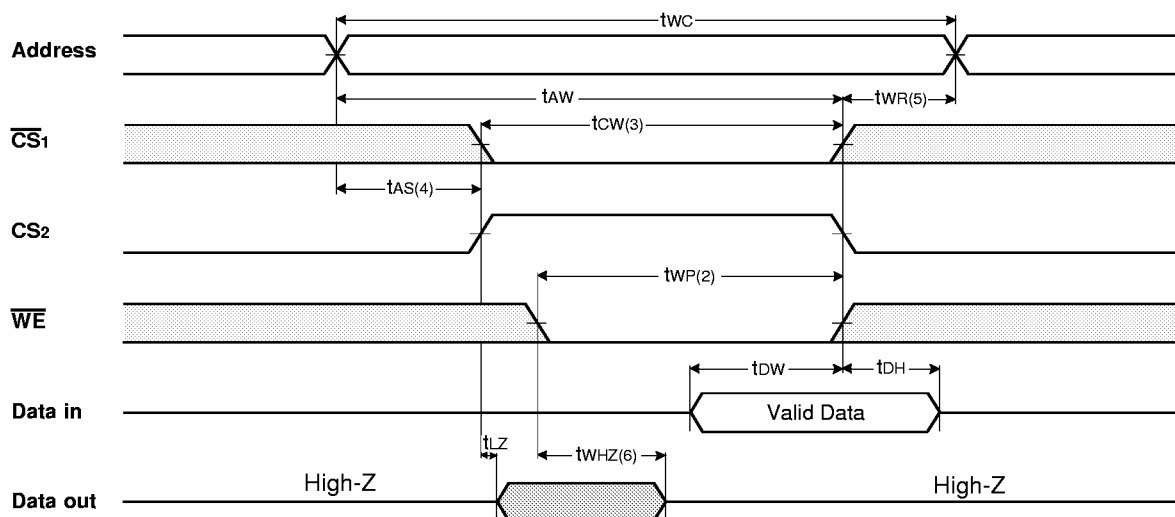
TIMING WAVEFORM OF WRITE CYCLE(1) ($\overline{OE}=\text{Clock}$)

TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{\text{OE}}$ =Low Fixed)



TIMING WAVEFORM OF WRITE CYCLE(3) ($\overline{\text{CS}}_1$ = Controlled)



TIMING WAVEFORM OF WRITE CYCLE(4) (CS₂ = Controlled)

NOTES(WRITE CYCLE)

1. All write cycle timing is referenced from the last valid address to the first transition address.
2. A write occurs during the overlap of a low $\overline{CS_1}$, a high $\overline{CS_2}$ and a low $\overline{WE}$. A write begins at the latest transition $\overline{CS_1}$ going low, $\overline{CS_2}$ going high and $\overline{WE}$ going low ; A write ends at the earliest transition $\overline{CS_1}$ going high or $\overline{CS_2}$ going low or $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of $\overline{CS_1}$ going low or $\overline{CS_2}$ going high to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR1} applied in case a write ends as $\overline{CS_1}$ or $\overline{WE}$ going high. t_{WR2} applied in case a write ends as $\overline{CS_2}$ going low.
6. If $\overline{OE}$, $\overline{CS_1}$, $\overline{CS_2}$ and $\overline{WE}$ are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If $\overline{CS_1}$ goes low and $\overline{CS_2}$ goes high simultaneously with $\overline{WE}$ going or after $\overline{WE}$ going low, the outputs remain high impedance state.
9. DOUT is the read data of the new address.
10. When $\overline{CS_1}$ is low and $\overline{CS_2}$ is high : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

FUNCTIONAL DESCRIPTION

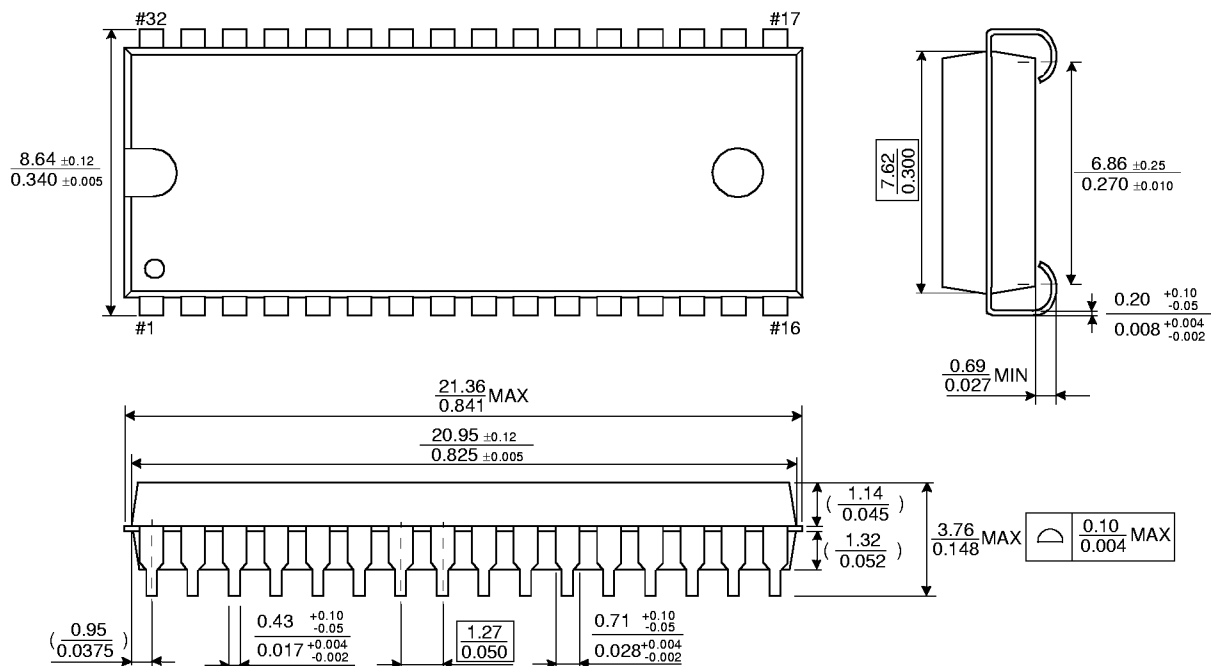
$\overline{CS_1}$	$\overline{CS_2}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O Pin	Supply Current
H	X	X	X*	Not Select	High-Z	I_{SB} , I_{SB1}
X	L	X	X	Not Select	High-Z	I_{SB} , I_{SB1}
L	H	H	H	Output Disable	High-Z	I_{CC}
L	H	H	L	Read	DOUT	I_{CC}
L	H	L	X	Write	DIN	I_{CC}

* NOTE : X means Don't Care.

CMOS SRAM

32-SOJ-300

Units: millimeters/Inches



Units: millimeters/Inches

